

ABSTRACT

In this heat treatment jig and method for silicon wafers, a silicon wafer is heat-treated while being mounted on support projections provided on three support arms, having an intervening spacing, protruding from a support frame towards the center. At that time, all the support projections under the silicon wafer are positioned on a same circle within a region where a radial distance from the center is defined by 85 to 99.5% of the wafer radius, and the support arms form an angle of 120° with each other about the center. With this jig and method, free depth of a dislocation generated from a pin position can be controlled deeper than a device formation region, and a widest slip-free region where the surface is free from slip dislocation is obtained.